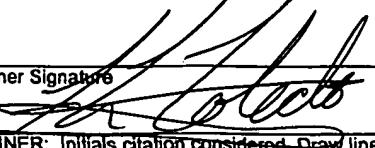


Substitute Form PTO-1449 (Modified)		U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 12732-158001	Application No. <u>10/603949</u> <u>New Application</u>
Information Disclosure Statement by Applicant (Use several sheets if necessary) (37 CFR §1.98(b))		Applicant Shigeharu Monoe		
		Filing Date June 26, 2003	Group Art Unit <u>2823</u>	

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Examiner Signature 	Date Considered <u>8/20/04</u>
EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	